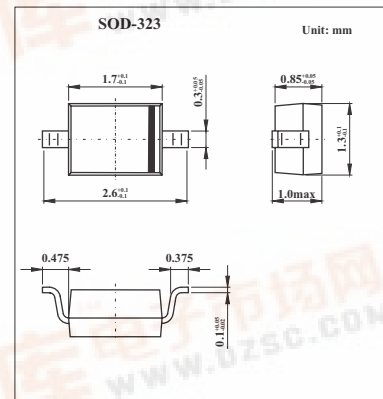


SMD Type Diodes

Silicon Schottky Diode BAT68-03W

■ Features

- For mixer applications in the VHF/UHF range
- For high speed switching



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	8	V
Forward current	I _F	130	mA
Total Power dissipation TS = 95 °C	P _{tot}	150	mW
Junction temperature	T _j	150	°C
Operating temperature range	T _{op}	-65 to +150	°C
Storage temperature	T _{stg}	-65 to +150	°C
Junction ambient	R _{thJA}	445	K/W
Junction - soldering point	R _{thJS}	365	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V _(BR)	I _(BR) = 10 μA	8			V
Reverse current	I _R	V _R = 1 V, T _A = 25°C			0.1	μA
		V _R = 1 V, T _A = 60°C			1.2	
Forward voltage	V _F	I _F = 1 mA		318	340	mV
		I _F = 10 mA	340	390	500	
Diode capacitance	C _T	V _R = 0 V, f = 1 MHz			1	pF
Differential forward resistance	R _F	I _F = 5 mA			10	Ω

Forward current I_F = f (T_A*; T_S)

*) : mounted on alumina 15mm x 16.7mm x 0.7mm

■ Marking

Marking	K
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